Title (en)

SINTERED SEMICONDUCTOR MATERIAL

Title (de)

GESINTERTES HALBLEITERMATERIAL

Title (fr)

MATERIAU SEMICONDUCTEUR OBTENU PAR FRITTAGE

Publication

EP 1618612 A1 20060125 (FR)

Application

EP 04742838 A 20040409

Priority

- FR 2004050151 W 20040409
- FR 0304676 A 20030414

Abstract (en)

[origin: WO2004093202A1] The invention relates to a method for forming a semiconductor material obtained by sintering powders and to a semiconductor material. The method comprises a compression and heat treatment stage such that one part of the powder is melted or becomes viscous. The material can be used in the photovoltaic field.

IPC 1-7

H01L 31/18; H01L 31/0236

IPC 8 full level

H01L 31/0236 (2006.01); **H01L 31/18** (2006.01)

CPC (source: EP US)

H01L 31/02363 (2013.01 - EP US); **H01L 31/1804** (2013.01 - EP US); Y02E 10/547 (2013.01 - EP US); Y02P 70/50 (2015.11 - EP US)

Citation (search report)

See references of WO 2004093202A1

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IT LI LU MC NL PL PT RO SE SI SK TR

DOCDB simple family (publication)

WO 2004093202 A1 20041028; EP 1618612 A1 20060125; JP 2006523021 A 20061005; JP 4869061 B2 20120201; US 2007178675 A1 20070802; US 8105923 B2 20120131

DOCDB simple family (application)

FR 2004050151 W 20040409; EP 04742838 A 20040409; JP 2006505871 A 20040409; US 55254804 A 20040409